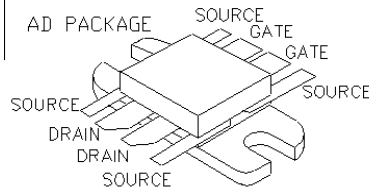




General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"TM process features gold metal for greatly extended lifetime. Low output capacitance and high F_t enhance broadband performance



PATENTED GOLD METALIZED SILICON GATE ENHANCEMENT MODE RF POWER VDMOS TRANSISTOR

80 Watts Push - Pull

Package Style AD

HIGH EFFICIENCY, LINEAR, HIGH GAIN, LOW NOISE

ABSOLUTE MAXIMUM RATINGS (TC = 25 °C)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
290 Watts	0.6 °C/W	200 °C	-65 °C to 150 °C	12 A	70 V	70V	30V

RF CHARACTERISTICS (80WATTS OUTPUT)

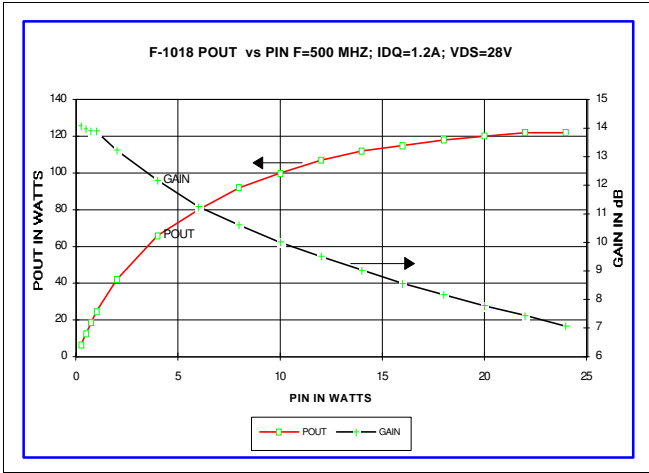
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	10			dB	Idq = 1.2 A, Vds = 28.0V, F = 500 MHz
η	Drain Efficiency		60		%	Idq = 1.2 A, Vds = 28.0V, F = 500 MHz
VSWR	Load Mismatch Toleranc			20:1	Relative	Idq = 1.2 A, Vds = 28.0V, F = 500 MHz

ELECTRICAL CHARACTERISTICS (EACH SIDE)

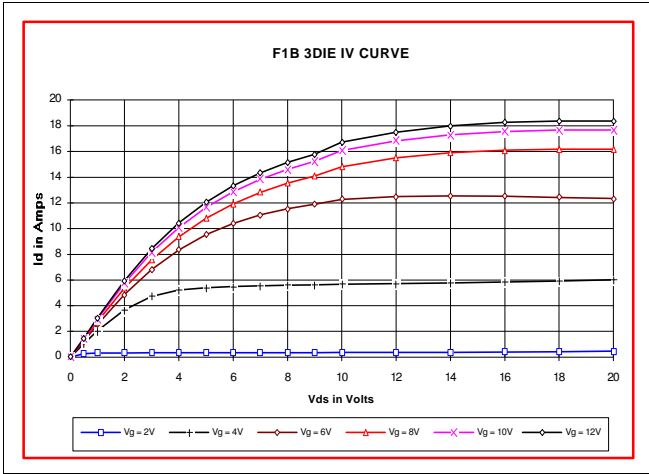
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltag	65			V	Ids = 0.15 A, Vgs = 0V
Idss	Zero Bias Drain Curren			3	mA	Vds = 28.0 V, Vgs = 0V
Igss	Gate Leakage Curren			1	uA	Vds = 0 V, Vgs = 30V
Vgs	Gate Bias for Drain Curren	1		7	V	Ids = 0.3 A, Vgs = Vds
gM	Forward Transconductanc		2.4		Mho	Vds = 10V, Vgs = 5V
Rdson	Saturation Resistanc		0.5		Ohm	Vgs = 20V, Ids = 12A
Idsat	Saturation Curren		16.5		Amp	Vgs = 20V, Vds = 10V
Ciss	Common Source Input Capacitanc		99		pF	Vds = 28.0 V, Vgs = 0V, F = 1 MHz
Crss	Common Source Feedback Capacitanc		12		pF	Vds = 28.0 V, Vgs = 0V, F = 1 MHz
Coss	Common Source Output Capacitanc		60		pF	Vds = 28.0 V, Vgs = 0V, F = 1 MHz

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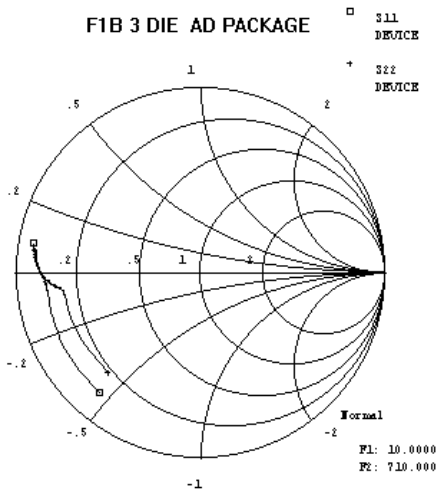
POUT VS PIN GRAPH



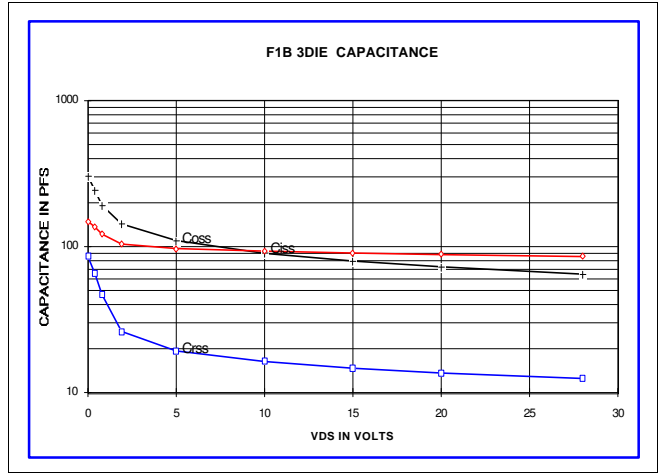
IV CURVE



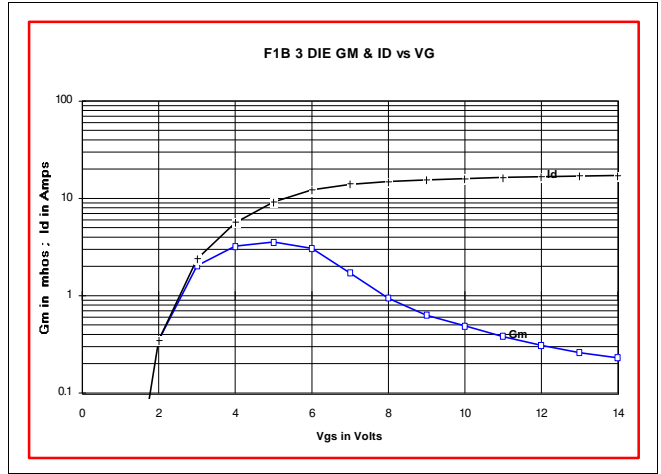
S11 AND S22 SMITH CHART



CAPACITANCE VS VOLTAGE



ID AND GM VS VGS



PACKAGE DIMENSIONS IN INCHES

